

Crystal Oscillator

Series CPWS

- Factory Programmable
- Standard Package Options
- Also available in 1.8V

Instrument Part Number:

CPWSC3LZ-A5B6-XX.XXXX TS

CPWS	C	3	L	Z	A7	B6	XX.XXXX	TS
SERIES	OUTPUT	PACKAGE STYLE	VOLTAGE	ADDED FEATURE	OPERATING TEMP	STABILITY	FREQUENCY	TRI-STATE
CPWS	C = CMOS	3 = 3.2 x 2.5 Ceramic 2 = 2.5 x 2.0 Ceramic	L = 3.3V R = 2.5V Q = 1.8V	Blank = Bulk Z = Tape and Reel	Blank = 0°C~+70°C A5 = -20°C~+70°C A7 = -40°C~+85°C	B6 = ±100PPM B9 = ±50PPM BR = ±25PPM	2.048 ~ 200.000	TS = Tri-State PD = Power Down

Specifications:

Description	Min	Typ	Max	Unit
Frequency Range: Programmable to any discrete frequency	2.048		200	V
Available Stability Options:	-50 -25		+50 +25	pF
Programmable Supply Voltage:				
(1-200MHz)	3.0	3.3	3.6	PPM
(1-166MHz)	2.2	2.5	2.8	PPM
(1-110MHz)	1.6	1.8	2.0	PPM
Operating Temperature Range:	-40		+85	
Storage Temperature:	-55		+125	
Aging: Ta=°25C,Vdd=3.3V			±5	PPM/Year

Operating Conditions:

Description	Min	Max	Unit
V _{DD} Supply Voltage	1.6	3.6	V
C _{CMOS} Max capacitive load on all outputs for CMOS levels		15	pF



Output Clock Switching Characteristics:

Description	Test Conditions	Min	Typ	Max	Unit
Duty Cycle:		45	-	55	%
Rise/Fall:	15pF	2	-	5	ns
Start Up Time	From Power On	-	-	2	ms
Peak to Peak*		-	80	-	Ps

* Jitter Tested at > 1,000,000 samples, exceeding JEDEC std JESD65



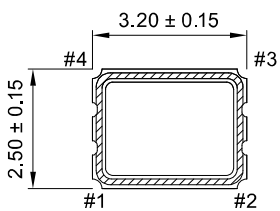
Electrical Characteristics:

Description	Test Conditions	Min	Typ	Max	Unit
Input Characteristics (Pin 1):					
V_{IL} , Low-Level Input Voltage (To Tri-State or Power Down)	$V_{DD} = 3.3V$	-	-	0.99	V
V_{IH} , High-Level Input Voltage (To Enable Output or Open)	$V_{DD} = 3.3V$	2	-	5	pF
I_{IL} , Input Low Current	$V_{IN} = 0V$	-	-	10	μA
I_{IH} , Input High Current	$V_{IN} = V_{DD}$	-	-	10	μA
Output Characteristics:					
V_{OL} , Low-Level Output Voltage	$V_{DD} = 3.3V$	-	-	0.33	V
	$V_{DD} = 2.5V$	-	-	0.25	V
	$V_{DD} = 1.8V$	-	-	0.18	V
$V_{IHC MOS}$, High-Level Output Voltage	$V_{DD} = 3.3V$	2.97	-	-	V
	$V_{DD} = 2.5V$	2.25	-	-	V
	$V_{DD} = 1.8V$	1.62	-	-	V
Power Supply Current: (Unloaded)	$2.048\text{ MHz} \leq F_O < 30\text{ MHz}$	6	-	15	mA
	$30\text{ MHz} \leq F_O < 75\text{ MHz}$	8	-	15	mA
	$75\text{ MHz} \leq F_O < 133\text{ MHz}$	12	-	20	mA
	$133\text{ MHz} \leq F_O < 166\text{ MHz}$	15	-	22	mA
	$166\text{ MHz} \leq F_O < 200\text{ MHz}$	-	-	25	mA
Standby Current:		-	10	15	μA
Tri-State Leakage Current	$V_{DD} = 3.3V$	-	-	50	μA
Output Enable Mode:	Output is Tri-Stated				
Power Down Mode:	Output is Tri-Stated				

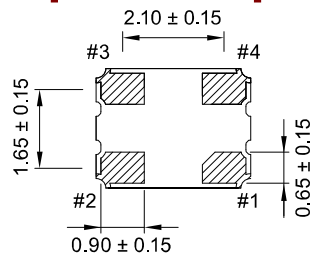
*Note: Bypass V_{DD} to GND with a 0.1pF capacitor

Style 3 3.2 x 2.5 Ceramic SMD

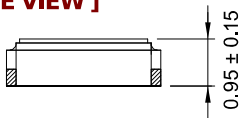
[TOP VIEW]



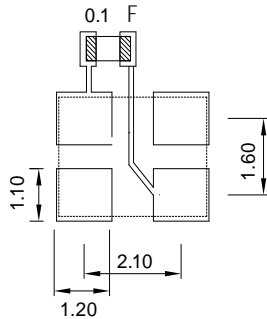
[BOTTOM VIEW]



[SIDE VIEW]

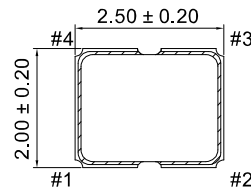


Pin#	Function
1	Tri-state
2	GND
3	Output
4	VDD

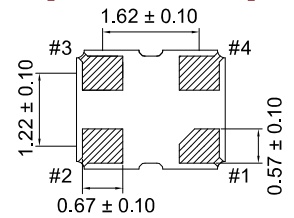


Style 2 2.5 x 2.0 Ceramic SMD

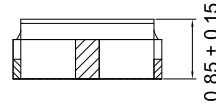
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[BOTTOM VIEW]



[SIDE VIEW]



Pin#	Function
1	Tri-state
2	GND
3	Output
4	VDD

